

ETCHING METHOD AND ETCHING APPARATUS

ABSTRACT

An etching method of the present disclosure includes: a first gas supply process of supplying a fluorine-containing gas during a first period into a processing container which accommodates a substrate on which a silicon oxide film is formed; a second gas supply process of supplying a basic gas into the processing container during a second period including a common supply period overlapping the first period; and a first exhaust process of exhausting an interior of the processing container so that a pressure within the processing container during the common supply period becomes a first pressure greater than 50 Torr to perform etching of the silicon oxide film by the fluorine-containing gas and the basic gas.

(Fig. 7)